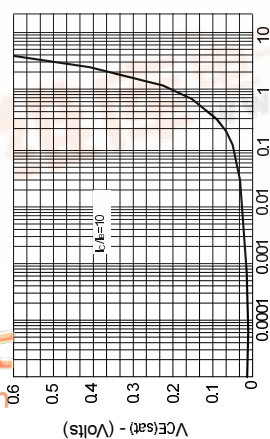


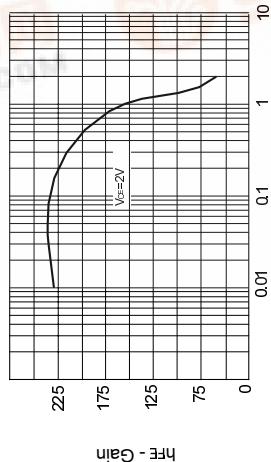


FZT753

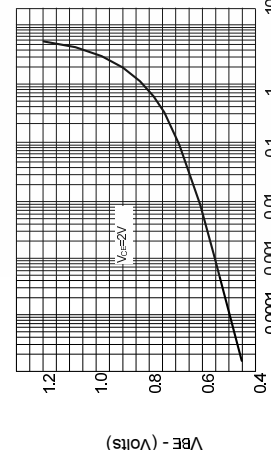
TYPICAL CHARACTERISTICS



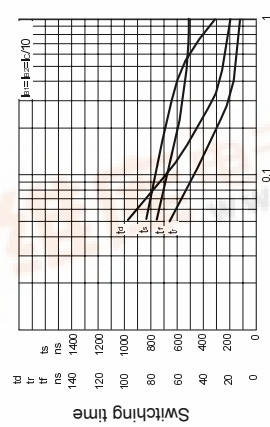
IC - Collector Current (Amps)
VCE(sat) v IC



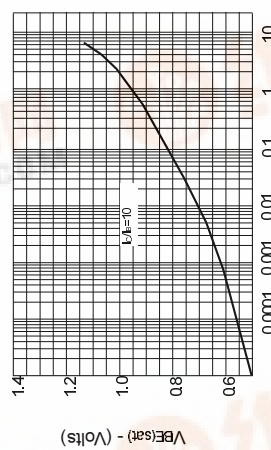
IC - Collector Current (Amps)
hFE v IC



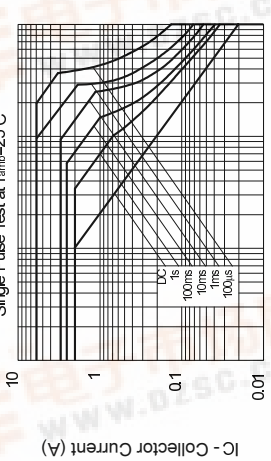
IC - Collector Current (Amps)
VBE(on) v IC



IC - Collector Current (Amps)
Switching Speeds



IC - Collector Current (Amps)
VBE(sat) v IC



VCE - Collector Emitter Voltage (V)
Safe Operating Area

SOT223 PNP SILICON PLANAR MEDIUM POWER TRANSISTOR

ISSUE 4 - FEBRUARY 1996

FEATURES

- * Low saturation voltage
- * Excellent h_{FE} specified up to 2A

COMPLEMENTARY TYPE - FZT653

PARTMARKING DETAIL - FZT753

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-120	V
Collector-Emitter Voltage	V_{CEO}	-100	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-6	A
Continuous Collector Current	I_C	-2	A
Power Dissipation at $T_{amb}=25^\circ\text{C}$	P_{tot}	2	W
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-120			V	$I_C = 100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-100			V	$I_C = 10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E = 100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			-0.1	μA	$V_{CB} = 100\text{V}$
Emitter Cut-Off Current	I_{EBO}			-10	μA	$V_{CB} = 100\text{V}, T_{amb} = 100^\circ\text{C}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.17	-0.3	V	$V_{EB} = 4\text{V}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-0.30	-0.5	V	$I_C = 1\text{A}, I_B = 100\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-0.9	-1.25	V	$I_C = 2\text{A}, I_B = 200\text{mA}^*$
Static Forward Current Transfer Ratio	h_{FE}	70	200	300		$I_C = 1\text{A}, V_{CE} = 2\text{V}^*$
Transition Frequency	f_T	100	140		MHz	$I_C = 50\text{mA}, V_{CE} = 2\text{V}^*$
Output Capacitance	C_{ob0}			30	pF	$I_C = 500\text{mA}, V_{CE} = 2\text{V}^*$
Switching Times	t_{on}		40		ns	$I_C = 1\text{A}, V_{CE} = 2\text{V}^*$
	t_{off}		600		ns	$I_C = 2\text{A}, V_{CE} = 2\text{V}^*$

*Measured under pulsed conditions. Pulse Width=300 μs . Duty cycle $\leq 2\%$
Spice parameter data is available upon request for this device

查询FZT753供应商

捷多邦, 专业PCB打样工厂, 24小时加急出货

**SOT223 PNP SILICON PLANAR
MEDIUM POWER TRANSISTOR**

ISSUE 4- FEBRUARY 1996

FEATURES

- * Low saturation voltage
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COMPLEMENTARY TYPE -- FZT653

PARTMARKING DETAIL - FZT753

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-120	V
Collector-Emitter Voltage	V_{CEO}	-100	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-6	A
Continuous Collector Current	I_C	-2	A
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	2	W
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to +150	$^{\circ}C$

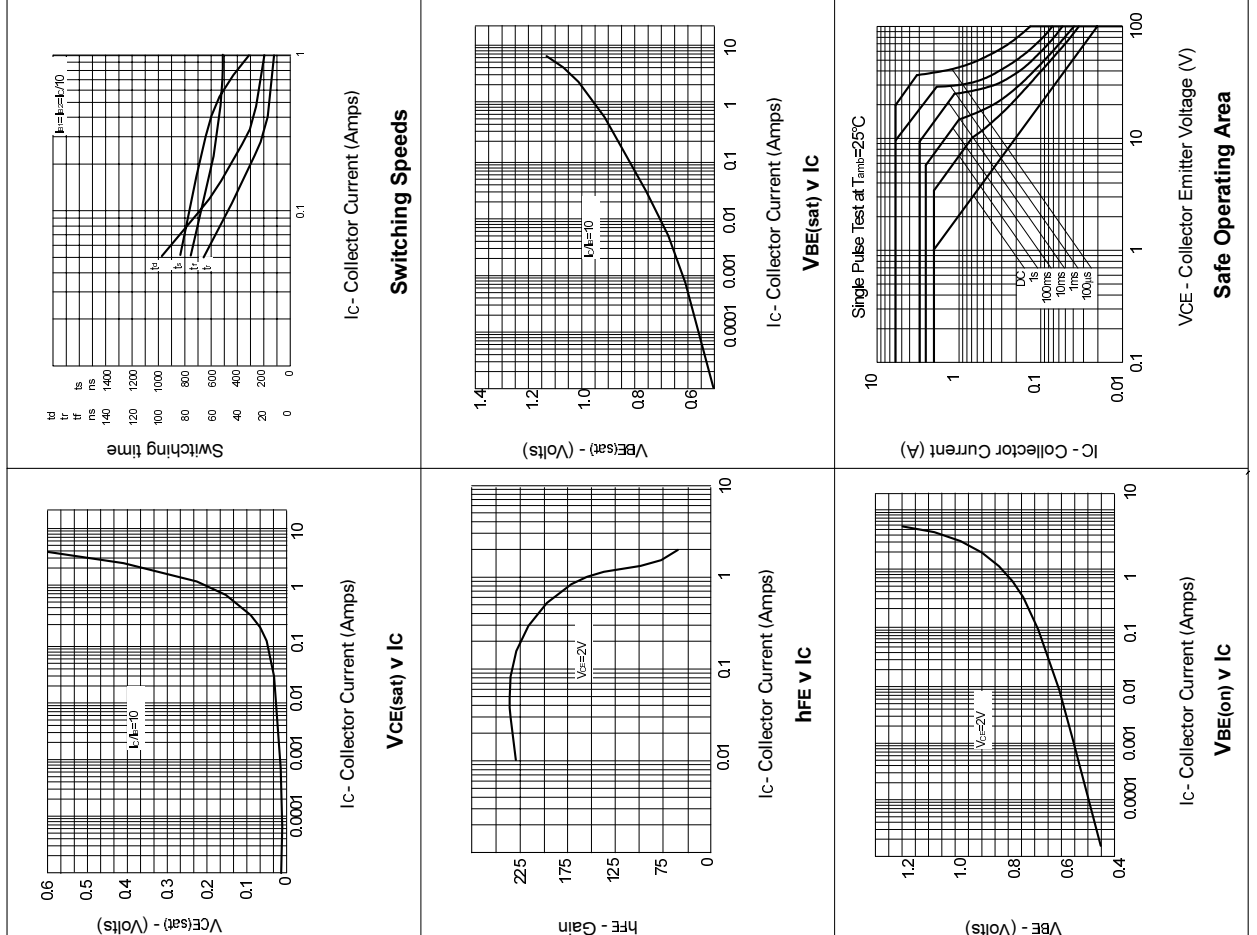
ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-120			V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-100			V	$I_C = 10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E = 100\mu A$
Collector Cut-Off Current	I_{CBO}			-0.1	μA	$V_{CE} = 100V$
Emitter Cut-Off Current	I_{EBO}			-10	μA	$V_{CE} = 100V, T_{amb} = 100^{\circ}C$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.17	-0.3	V	$V_{EB} = 4V$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-0.30	-0.5	V	$I_C = 1A, I_B = 100mA^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-0.9	-1.25	V	$I_C = 2A, I_B = 200mA^*$
Static Forward Current Transfer Ratio	h_{FE}	70	200	300		$I_C = 1A, V_{CE} = 2V^*$
Transition Frequency	f_T	100	140		MHz	$I_C = 1A, I_B = 100mA^*$
Output Capacitance	C_{obo}			30	pF	$V_{CE} = 10V, f = 1MHz$
Switching Times	t_{on}		40		ns	$I_C = 500mA, V_{CC} = 10V$
	t_{off}		600		ns	$I_B = I_{BZ} = 50mA$

*Measured under pulsed conditions. Pulse Width=300 μ s. Duty cycle $\leq 2\%$
Spice parameter data is available upon request for this device

FZT753

TYPICAL CHARACTERISTICS



FZT753

